

**Type 2N6193**  
**Geometry 9700**  
**Polarity PNP**  
**Qual Level: JAN - JANTXV**

**Generic Part Number:**  
**2N6193**

**REF: MIL-PRF-19500/561**

**Features:**

[Request Quotation](#)

- Silicon transistor for use in switching applications.
- Housed in a [TO-39](#) case.
- Also available in chip form using the [9700](#) chip geometry.
- The Min and Max limits shown are per [MIL-PRF-19500/561](#) which Semicoa meets in all cases.



**Maximum Ratings**

$T_C = 25^{\circ}\text{C}$  unless otherwise specified

Rating	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CEO}$	100	V
Collector-Base Voltage	$V_{CBO}$	100	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current, Continuous	$I_C$	5.0	A
Base Current, Continuous	$I_B$	1.0	A
Power Disipation $T_A = 25^{\circ}\text{C}$ ambient Derate above $25^{\circ}\text{C}$	$P_T$	1.0 5.71	W $\text{mW}/^{\circ}\text{C}$
Power Disipation $T_A = 25^{\circ}\text{C}$ ambient Derate above $25^{\circ}\text{C}$	$P_T$	10.0 57.1	Watt $\text{mW}/^{\circ}\text{C}$
Operating Junction Temperature	$T_J$	-55 to +200	$^{\circ}\text{C}$
Storage Temperature	$T_{STG}$	-55 to +200	$^{\circ}\text{C}$

## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise specified

OFF Characteristics	Symbol	Min	Max	Unit	
Collector-Emitter Breakdown Voltage $I_C = 50\text{ mA}$ , pulsed	$V_{(BR)CEO}$	100	---	V	
Collector-Base Cutoff Current $V_{CB} = 100\text{ V}$	$I_{CBO}$	---	10	$\mu\text{A}$	
Base-Emitter Cutoff Current $V_{EB} = 6\text{ V}$	$I_{EBO}$	---	100	$\mu\text{A}$	
	$V_{EB} = 5.5\text{ V}$ , $I_C = 0$	$I_{EBO2}$	---	1.0	$\text{mA}$
Collector-Emitter Cutoff Current $V_{CE} = 100\text{ V}$	$I_{CEO}$	---	100	$\mu\text{A}$	
	$V_{CE} = 90\text{ V}$ , $V_{BE} = 1.5\text{ V}$	$I_{CEX1}$	---	10	$\mu\text{A}$
	$V_{CE} = 90\text{ V}$ , $V_{BE} = 1.5\text{ V}$ , $T_A = +150^\circ\text{C}$	$I_{CEX2}$	---	1.0	$\text{mA}$

ON Characteristics	Symbol	Min	Max	Unit
<b>Forward Current Transfer Ratio</b>				
$I_C = 0.5\text{ A}$ , $V_{CE} = 2.0\text{ V}$ , pulsed	$h_{FE1}$	60	---	---
$I_C = 2.0\text{ A}$ , $V_{CE} = 2.0\text{ V}$ , pulsed	$h_{FE2}$	60	240	---
$I_C = 5.0\text{ A}$ , $V_{CE} = 2.0\text{ V}$ , pulsed	$h_{FE3}$	40	---	---
$I_C = 2.0\text{ A}$ , $V_{CE} = 2.0\text{ V}$ pulsed, $T_C = -55^\circ\text{C}$	$h_{FE4}$	12	---	---
<b>Base-Emitter Saturation Voltage</b>				
$I_C = 2.0\text{ A}$ , $I_B = 0.2\text{ A}$ , pulsed	$V_{BE(sat)1}$	---	1.2	V dc
$I_C = 5.0\text{ A}$ , $I_B = 0.5\text{ A}$ , pulsed	$V_{BE(sat)2}$	---	1.8	V dc
<b>Collector-Emitter Saturation Voltage</b>				
$I_C = 2.0\text{ A}$ , $I_B = 0.2\text{ A}$ , pulsed	$V_{CE(sat)1}$	---	0.7	V dc
$I_C = 5.0\text{ A}$ , $I_B = 0.5\text{ A}$ , pulsed	$V_{CE(sat)2}$	---	1.2	V dc

Small Signal Characteristics	Symbol	Min	Max	Unit
Magnitude of Common Emitter Small Signal Short Circuit Forward Current Transfer Ratio $V_{CE} = 5\text{ V}$ , $I_C = 0.5\text{ A}$ , $f = 10\text{ MHz}$	$ h_{fe} $	3.0	15	---
Input Capacitance, Output Open Circuited $V_{CB} = 10\text{ V}$ , $I_E = 0$ , $100\text{ kHz} < f < 1\text{ MHz}$	$C_{iBO}$	---	1250	$\text{pF}$
Open Circuit Output Capacitance $V_{CB} = 10\text{ V}$ , $I_E = 0$ , $100\text{ kHz} < f < 1\text{ MHz}$	$C_{oBO}$	---	300	$\text{pF}$

Switching Time	Symbol	Min	Max	Unit
Delay Time Per figure 5, MIL-PRF-19500/561B	$t_d$	---	100	ns
Rise Time Per figure 5, MIL-PRF-19500/561B	$t_r$	---	100	ns
Storage Time Per figure 5, MIL-PRF-19500/561B	$t_s$	---	2	ns
Fall Time Per figure 5, MIL-PRF-19500/561B	$t_f$	---	200	ns